

# STPS40100HR

### Aerospace 2 x 20 A - 100 V Schottky rectifier

#### Features

- Forward current: 2 x 20 A
- Repetitive peak voltage: 100 V
- Low forward voltage drop: 0.9 V
- Maximum junction temperature: 175 °C
- Negligible switching losses
- Low capacitance
- High reverse avalanche surge capability
- Hermetic packages
- Target radiation qualification:
  - 150 krad (Si) low dose rate
  - 1 Mrad high dose rate
- ESCC qualified



### Description

This power Schottky rectifier is designed and packaged to comply with the ESCC5000 specification for aerospace products. Housed in hermetically sealed packages both surface mount and through hole, it is ideal for use in applications for aerospace and other harsh environments.

The STPS40100HR is intended for use in medium voltage application and particularly, in high frequency circuits where low switching losses and low noise are required.

#### Table 1. Device summary

Order code	ESCC detailed specification	Quality level	Configuration	Package	Mass	EPPL
STPS40100C2FSY1	-	Engineering model	Double die, common cathode	T0-254	10.0 g	-
STPS40100C2FSYHR	5106/019/01	ESCC flight	pin 2			Y

## 1 Characteristics

Table 2.	Absolute	maximum	ratings
	Absolute	maximam	radings

Symbol	Characteristic	Value	Unit
I <sub>FSM</sub>	Forward surge current (per diode) <sup>(1)</sup>	300	А
$V_{RRM}$	Repetitive peak reverse voltage <sup>(2)</sup>	100	V
I <sub>RRM</sub>	Repetitive peak reverse current <sup>(3)</sup>	1	А
I <sub>o</sub>	Average output rectified current (50% duty cycle): <sup>(4)</sup> , <sup>(5)</sup> per diode per device	20 40	A
I <sub>F(RMS)</sub>	Forward rms current (per diode)	30	А
T <sub>OP</sub>	Operating temperature range <sup>(6)</sup> (case temperature)	-65 to +175	°C
Τ <sub>J</sub>	Junction temperature	+175	°C
T <sub>STG</sub>	Storage temperature range <sup>(6)</sup>	-65 to +175	°C
T <sub>SOL</sub>	Soldering temperature: For TO-254 <sup>(7)</sup>	+260	°C
dV/dt	Critical rate of rise of reverse voltage	10000	V/µs

1. Sinusoidal pulse of 10 ms duration

- 2. Pulsed, duration 5 ms, F = 50 Hz
- 3. Pulsed, duration 2  $\mu$ s, F = 1 kHz
- 4. For  $T_{case} \ge +132^{\circ}C$  per device and  $T_{case} \ge +148^{\circ}C$  per diode, derate linearly to 0 A at +175°C.
- 5. The "per device" ratings apply only when both anode terminals are tied together.
- 6. For devices with hot solder dip lead finish all testing performed at  $T_{amb}$  > +125 °C are carried out in a 100% inert atmosphere.
- 7. Duration 10 seconds maximum at a distance of not less than 1.5 mm from the device body and the same lead shall not be resoldered until 3 minutes have elapsed.

Table 3. Thermal resistance

Symbol	Characteristic	Value	Unit
$R_{th(j-c)}^{(1)}$	Thermal resistance, junction to case per diode per device	1.5 1.2	°C/W

1. Package mounted on infinite heatsink



Symbol	Characteristic	MIL-STD-750	Test conditions	Val	Unite		
Symbol	Symbol	Characteristic	test method	Test conditions	Min.	Max.	Units
I <sub>R1</sub>	Boverse current	4016	DC method, V <sub>R</sub> = 100 V	-	30	μA	
I <sub>R2</sub>		4010	DC method, V <sub>R</sub> = 50 V	-	5	μA	
V <sub>F1</sub> <sup>(1)</sup>			Pulse method, I <sub>F</sub> = 5 A	-	610	mV	
V <sub>F2</sub> <sup>(1)</sup>	Forward voltage	4011	Pulse method, I <sub>F</sub> = 10 A	- 730	mV		
V <sub>F3</sub> <sup>(1)</sup>			Pulse method, I <sub>F</sub> = 20 A	-	900	mV	
С	Capacitance	4001	V <sub>R</sub> = 10 V, F = 1 MHz	-	1	nF	
Z <sub>th(j-c)</sub> <sup>(2)</sup>	Relative thermal impedance, junction to case	3101	$I_{H} = 15 \text{ to } 40 \text{ A}, t_{H} = 50 \text{ ms}$ $I_{M} = 50 \text{ mA}, t_{md} = 100 \mu\text{s}$	Calculat	te $\Delta V_F^{(3)}$	°C/W	

Table 4.	Electrical measurements at ambiant temperature (per diode), $T_{amb} = 22 \pm 3$	°C
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1. Pulse width  $\leq 300 \mu s, \, duty \, cycle \leq 2\%$ 

2. Performed only during screening tests parameter drift values (initial measurements for HTRB), go-no-go.

3. The limits for  $\Delta VF$  shall be defined by the manufacturer on every lot in accordance with MIL-STD-750 Method 3101 and shall guarantee the  $R_{th(j-c)}$  limits specified in maximum ratings.

Symbol	Characteristic	MIL-STD-750	Toot conditions <sup>(1)</sup>	Val	ies Max.	Unito
Symbol	Characteristic	test method	Test conditions.	Min.	Max.	Units
I <sub>R1</sub>	Poverse current	1010	$T_{case} = +125 (+0, -5) °C$ DC method, V <sub>R</sub> = 100 V	-	20	mA
I <sub>R2</sub>		4010	$T_{case} = +125 (+0, -5) °C$ DC method, V <sub>R</sub> = 50 V	-	7.5	mA
V <sub>F2</sub> <sup>(2)</sup>		4011	$T_{case} = +125 (+0, -5) °C$ pulse method, I <sub>F</sub> = 10 A	-	660	mV
V <sub>F3</sub> <sup>(2)</sup>	Forward voltage		$T_{case} = +125 (+0, -5) °C$ pulse method, I <sub>F</sub> = 20 A	-	850	mV
			$T_{case} = -55 (+5, -0) °C$ pulse method, I <sub>F</sub> = 20 A	-	950	mV

Table 5. Electrical measurements at high and low temperatures (per dic	ode)
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1. Read and record measurements shall be performed on a sample of 5 components with 0 failures allowed. Alternatively a 100% inspection may be performed.

2. Pulse width  $\leq$  300µs, duty cycle  $\leq$  2%



## 2 Configurations







### 3 Package Information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK<sup>®</sup> is an ST trademark.



#### Figure 2. Metal flange mount package (TO-254<sup>(a)</sup>), 3 lead dimension definitions

a. The terminal identification is specified by the device configuration. See *Figure 1* for terminal connections



Deference	Dimension in	Dimension in millimetres		n in inches	
Reference	Min.	Max.	Min.	Max.	
А	13.59	13.84	0.535	0.545	
В	13.59	13.84	0.535	0.545	
С	20.07	20.32	0.790	0.800	
D	6.3	6.7	0.248	0.264	
E	1	3.9	0.039	0.154	
ØF	3.5	3.9	0.138	0.154	
G	16.89	17.4	0.665	0.685	
Н	6.86	BSC	0.270 BSC		
ØI <sup>(1)</sup>	0.89	1.14	0.035	0.045	
J	3.81	BSC	0.150 BSC		
К	3.81	BSC	0.150 BSC		
L	12.95	14.5	0.510	0.571	
ØM	3.05 Тур.		0.120 Тур.		
Ν	-	0.71	-	0.028	
R1 <sup>(2)</sup>	-	1	-	0.039	
R2 <sup>(3)</sup>	1.65	Тур.	0.0	065	

 Table 6.
 Metal flange mount package (TO-254), 3-lead dimension values

1. 3 locations

2. Radius of heatsink flange corner - 4 locations

3. Radius of body corner - 4 locations



## 4 Ordering Information

#### Table 7. Ordering information

Order code	ESCC detailed specification	Package	Lead finish	Marking	EPPL	Mass (g)	Packing
STPS40100C2FSY1	-	TO-254	Gold	STPS40100C2FSY1 + BeO	-	10.0	Strip
STPS40100C2FSYHR	5106/019/01		Solder dip	510601901 + BeO	Y		μασκ



## 5 Revision history

#### Table 8.Document revision history

Date	Revision	Changes
26-Mar-2010	1	Initial release.



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